



1. Description

SS028N08MS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for BMS and high current switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	85	V
I_D	180	A
$R_{DS(on).typ}$	2.4	mΩ

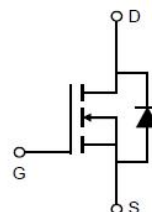
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 2.8m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

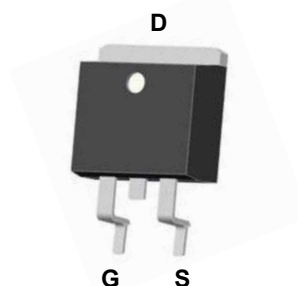
APPLICATIONS

- BMS
- High current switching applications
- DC-DC Converter

Schematic Diagram



TO-263-2L top view



ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS028N08MS	TO-263	SS028N08MS	Reel